

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	99223	(wide\$1gap wide near2 gap sic silicon near4 carbide)	US-PGPUB; USPAT	OR	ON	2007/04/19 16:30
L2	89	1 same ((built\$1in)adj (potential voltage))	US-PGPUB; USPAT	OR	ON	2007/04/19 16:58
L3	84	(heat temperature sink dissipat\$4)and 2	US-PGPUB; USPAT	OR	ON	2007/04/19 16:32
L4	10	(heat temperature sink dissipat\$4)same 2	US-PGPUB; USPAT	OR	ON	2007/04/19 16:39
L5	1619	((heat) near2 (sink dissipat\$4))same 1	US-PGPUB; USPAT	OR	ON	2007/04/19 16:55
L6	726	(diode\$2 bpt bi\$1polar) and 5	US-PGPUB; USPAT	OR	ON	2007/04/19 16:55
L7	733	(diode\$2 bpt bi\$1polar pn\$1junction\$2 pn adj junction) and 5	US-PGPUB; USPAT	OR	ON	2007/04/19 16:36
L8	102	(sic silicon adj carbide)adj2 (element device) and 7	US-PGPUB; USPAT	OR	ON	2007/04/19 16:40
L9	23	(gamma adj ray\$2 electron adj beam particle near3 beam\$2 temperature near4 degree\$2)and 8	US-PGPUB; USPAT	OR	ON	2007/04/19 16:38
L10	902	((heat) near2 (sink))same 1	US-PGPUB; USPAT	OR	ON	2007/04/19 16:39
L11	436	(diode\$2 bpt bi\$1polar) and 10	US-PGPUB; USPAT	OR	ON	2007/04/19 16:39
L12	57	(sic silicon adj carbide)adj2 (element device) and 11	US-PGPUB; USPAT	OR	ON	2007/04/19 16:56
L13	39	12 not 9	US-PGPUB; USPAT	OR	ON	2007/04/19 16:54
L14	4421	(wide\$1gap wide near gap sic silicon near4 carbide)same (built\$1in voltage)	US-PGPUB; USPAT	OR	ON	2007/04/19 16:59
L15	495	((heat) near2 (sink dissipat\$4))and 14	US-PGPUB; USPAT	OR	ON	2007/04/19 16:57
L16	128	(bpt bi\$1polar) and 15	US-PGPUB; USPAT	OR	ON	2007/04/19 16:59
L17	48	(sic silicon adj carbide)adj2 (element device) and 16	US-PGPUB; USPAT	OR	ON	2007/04/19 17:02
L18	36	17 not 13	US-PGPUB; USPAT	OR	ON	2007/04/19 16:57
L19	277	((heat) near2 (sink))and 14	US-PGPUB; USPAT	OR	ON	2007/04/19 16:59
L20	57	(bpt bi\$1polar) and 19	US-PGPUB; USPAT	OR	ON	2007/04/19 16:57

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L21	45	20 not 13	US-PGPUB; USPAT	OR	ON	2007/04/19 16:57
L22	31	21 not 17	US-PGPUB; USPAT	OR	ON	2007/04/19 16:57
L23	271	(wide\$1gap wide near gap sic silicon near4 carbide)and ((built\$1in)adj (potential voltage))	US-PGPUB; USPAT	OR	ON	2007/04/19 16:59
L24	122	(bpt bi\$1polar) and 23	US-PGPUB; USPAT	OR	ON	2007/04/19 16:59
L25	3	((heat) near2 (sink))and 24	US-PGPUB; USPAT	OR	ON	2007/04/19 17:08
L26	10	((built\$1in)adj (potential voltage))and (wide\$1gap wide near gap sic silicon near4 carbide)	EPO; JPO; DERWENT	OR	ON	2007/04/19 17:06
L27	66	(sic silicon adj carbide)adj2 (element device) and ((built\$1in)adj (potential voltage))	US-PGPUB; USPAT	OR	ON	2007/04/19 17:20
L28	62084	((heat) near2 (sink))and27	US-PGPUB; USPAT	OR	ON	2007/04/19 17:02
L29	3	((heat) near2 (sink))and 27	US-PGPUB; USPAT	OR	ON	2007/04/19 17:03
L30	3	(wire adj (bonded bonding bond) or flip) and 27	US-PGPUB; USPAT	OR	ON	2007/04/19 17:04
L31	5	27 and packag\$4	US-PGPUB; USPAT	OR	ON	2007/04/19 17:05
L32	38	(bpt bi\$1polar) and (sic silicon adj carbide)adj2 (element device) and packag\$4 and (wire adj (bonded bonding bond) or flip) and (heat temperature sink)	US-PGPUB; USPAT	OR	ON	2007/04/19 17:06
L33	38	(bpt bi\$1polar) and (sic silicon adj carbide)adj2 (element device) and packag\$4 and (wire adj (bonded bonding bond) or flip) and (heat\$4 temperature sink)	US-PGPUB; USPAT	OR	ON	2007/04/19 17:06
L34	1920	((built\$1in)adj (potential voltage))	US-PGPUB; USPAT	OR	ON	2007/04/19 17:06
L35	45	((wide\$1gap wide near gap sic silicon near4 carbide)same (built\$1in voltage)same (gamma adj ray\$2 electron adj beam particle near3 beam\$2 temperature near4 degree\$2 heat\$4)).ab,clm.	US-PGPUB; USPAT	OR	ON	2007/04/19 17:09
L36	633	257/170-171 257/147 257/584.ccls.	US-PGPUB; USPAT	OR	OFF	2007/04/19 17:12
L37	17	34 and 36	US-PGPUB; USPAT	OR	OFF	2007/04/19 17:19

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L38	11	((sic silicon adj carbide)adj2 (element device)) same ("V.sub.f")	US-PGPUB; USPAT	OR	ON	2007/04/19 17:15
L39	546	257/E23.08 257/E29.212.ccls.	US-PGPUB; USPAT	OR	ON	2007/04/19 17:18
L40	9	34 and 39	US-PGPUB; USPAT	OR	OFF	2007/04/19 17:19
L41	5	(sic silicon adj carbide)and 40	US-PGPUB; USPAT	OR	ON	2007/04/19 17:20